

NPN Triple Diffused Planar Silicon Transistor

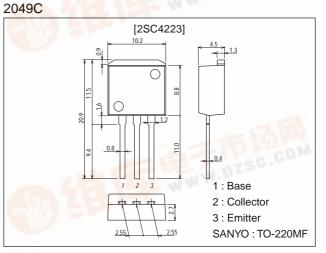


Features

- · High breakdown voltage, high reliability.
- \cdot Fast switching speed (t_f=0.1µs typ).
- \cdot Wide ASO.
- · Adoption of MBIT process.
- Suitable for sets whose height is restricted.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1100	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	ΙC		1.5	А
Collector Current (Pulse)	ICP	PW≤300µs, duty cycle≤10%	5	А
Base Current	Ι _Β		0.8	А
Collector Dissipation	PC	Ta=25°C	1.65	W
		Tc=25°C	40	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Onit
Collector Cutoff Current	ICBO	V _{CB} =800V, I _E =0		1 -37	10	μA
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0	10-		10	μA
DC Current Gain	h _{FE} 1	V _{CE} =5V, I _C =0.1A	10*	0.0	40*	
	h _{FE} 2	V _{CE} =5V, I _C =0.5A	8			

*: The h_{FE}l of the 2SC4223 is classified as follows. When specifying the h_{FE}l rank, specify two ranks or more in principle.

10 K 20 15 L 30 20 M 40

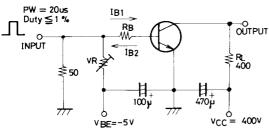
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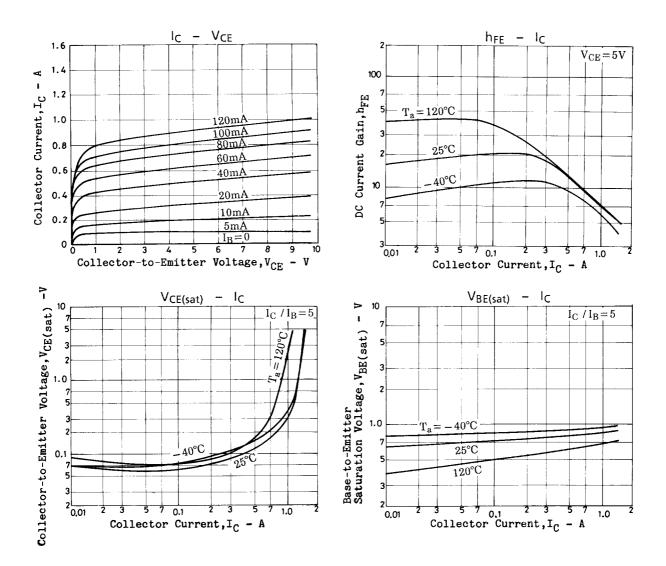
2SC4223

Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Unit
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =0.1A		15		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		35		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =0.75A, I _B =0.15A			2.0	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =0.75A, I _B =0.15A			1.5	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =1mA, I _E =0	1100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =5mA, R _{BE} =∞	800			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =1mA, I _C =0	7			V
Collector-to-Emitter Sustain Voltage	VCEX(sus)	I _C =0.75A, I _{B1} =-I _{B2} =0.15A, L=5mH, clamped	800			V
Turn-ON Time	ton	I_{C} =1A, I_{B1} =0.2A, I_{B2} =-0.4A, R_{L} =400 Ω , V_{CC} =400V			0.5	μs
Storage Time	^t stg	I_{C} =1A, I_{B1} =0.2A, I_{B2} =-0.4A, R_{L} =400 Ω , V_{CC} =400V			3.0	μs
Fall Time	tf	I _C =1A, I _{B1} =0.2A, I _{B2} =-0.4A, R _L =400Ω, V _{CC} =400V			0.3	μs

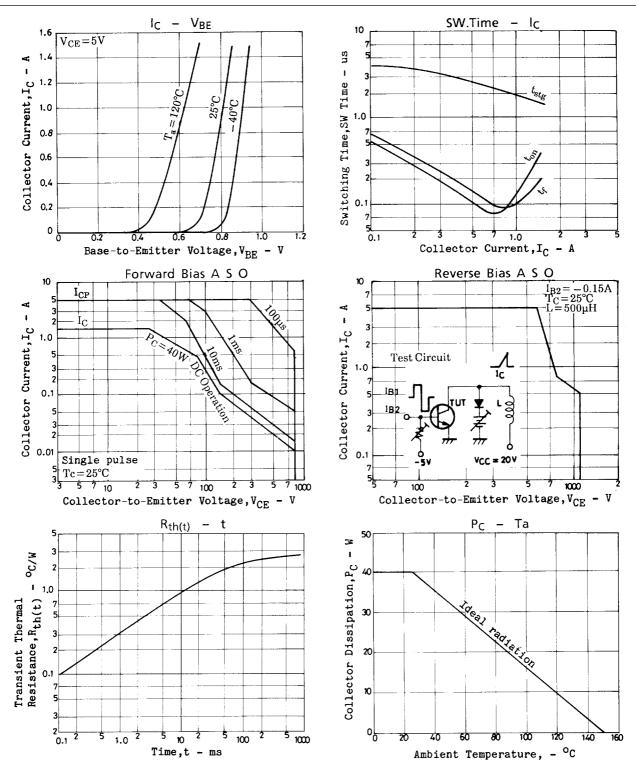
Switching Time Test Circuit



Dy Unit (resistance: Ω, capacitance: F)



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